

# Biexcitons in II-VI crystals

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The existence of biexciton states at high excitation intensities has been experimentally established in crystals CdS and CdSe with binding energies 2.5 meV (CdS) and 1.2 meV (CdSe).

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1. It is believed, as a result of a number of investigations by Shionoya's group, that biexcitons in hexagonal II-VI crystals are the cause of the *M* emission band<sup>[1]</sup> produced at high excitation intensities and situated on the low-energy side of the well known line *I*<sub>2</sub>, which is due to excitons bound by neutral donors. There are serious objections to this interpretation in<sup>[2,4]</sup>, where the *M* band is not attributed to biexciton emission and is explained as being due to other mechanisms. The main arguments against the biexciton interpretation are the excessively large binding energy<sup>[1]</sup> in comparison with the theoretically predicted value,<sup>[5]</sup> the presence of a chemical shift<sup>[2,3]</sup> (dependence on the spectral position of the *I*<sub>2</sub> line), and the possibility of a different interpretation of the phenomenon.<sup>[3,4]</sup> Thus, the question of the biexciton state in II-VI crystals must be reviewed anew.

2. We prove in this paper the existence of biexcitons in II-VI compounds and show that their radiative decay corresponds to a different spectral singularity, the so called *P* line previously attributed to Auger recombination of two free excitons.<sup>[1]</sup>

Figure 1 shows the emission spectrum of a CdS crystal excited by an LGI-21

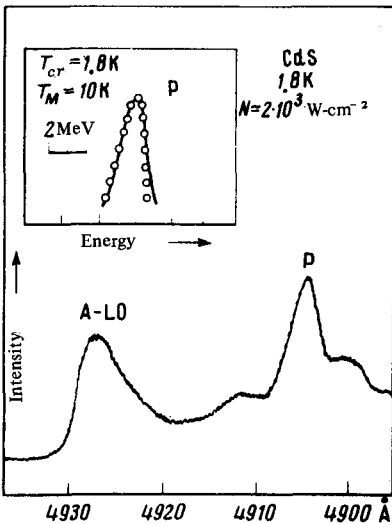


FIG. 1. Emission spectrum of CdS crystal at high excitation intensity. The insert shows a comparison of the experimental contour of the *P* line (solid line) with the Maxwellian-distribution contour (points).

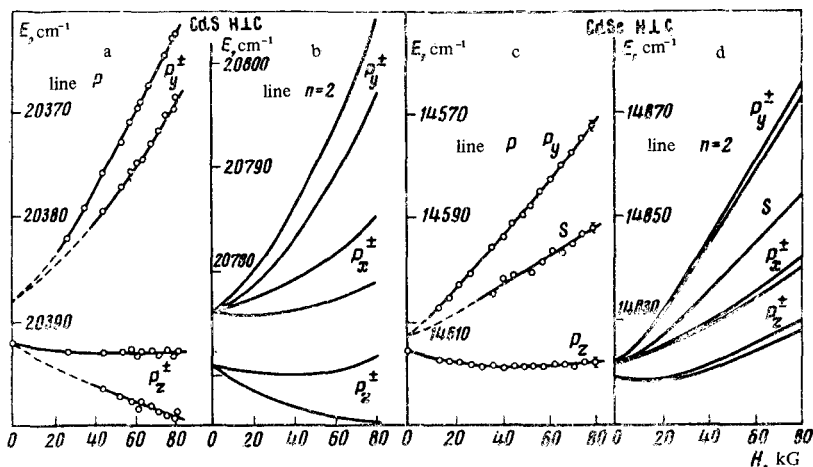


FIG. 2. Energy positions of the  $P$  lines (a, c) and of the  $n=2$  lines of the free excitation (b, d) vs the magnetic field ( $H \perp c$ ) for the crystals CdS (a, b) and CdSe (c, d).

nitrogen laser. A detailed analysis of the spectral position of the line  $P$  ( $\lambda = 4904.5 \text{ \AA}$ ) has shown that it can be attributed to biexciton radiative decay with transition of the remaining exciton to an excited state  $A, n=2$ . An analogous line  $P$  ( $\lambda = 6842 \text{ \AA}$ ) was observed by us in the CdSe crystal. The contours of the  $P$  lines are characterized by a reciprocal Maxwellian distribution, corresponding to a biexciton temperature  $\sim 10 \text{ K}$  (CdS) or  $\sim 20 \text{ K}$  (CdSe). The binding energies of the biexcitons, determined from the spectral shifts of the  $P$  lines relative to the exciton level  $A_T(\Gamma_5^-)$ , are equal to 2.5 meV (CdS) and 1.2 meV (CdSe). These quantities are close to the theoretically expected<sup>[5]</sup> 2.6 meV (CdS) and 1.3 meV (CdSe), and agree with the rapid temperature vanishing of the  $P$  lines. The intensity of these lines increases superlinearly with increasing excitation intensity.

3. A magneto-optical investigation was carried out to confirm the hypothesis based on the aforementioned experimental facts, that the  $P$  lines are of biexciton origin. We have observed a complex splitting of these lines (CdS, CdSe) in a magnetic field (see Fig. 2). Comparison of the pictures of the Zeeman splitting of the  $P$  line and of the absorption line  $n=2$ <sup>1)</sup> for both orientations of the magnetic fields,  $H \perp c$  and  $H \parallel c$ , has made it possible to interpret unambiguously the observed terms and to prove that the final state at which the transition terminates is indeed the level  $n=2$  of the free exciton. The symbols for the smooth components on Fig. 2 pertain to the terms of the level  $n=2$  to which the transitions take place. As seen from Fig. 3, the  $P$  lines are split with exactly the same  $g$  factors as the  $n=2$  line. This fact denies the possibility of attributing the  $P$  line to Auger recombination of the bound excitons,<sup>[8]</sup> which is characterized by an entirely different picture of the Zeeman splitting.

The identification of the final state ( $n=2$  of the free electron) in the  $P$  transition has enabled us to determine the behavior of the initial (biexciton) state in a magnetic field. No splitting of the biexciton level was observed, but a strong

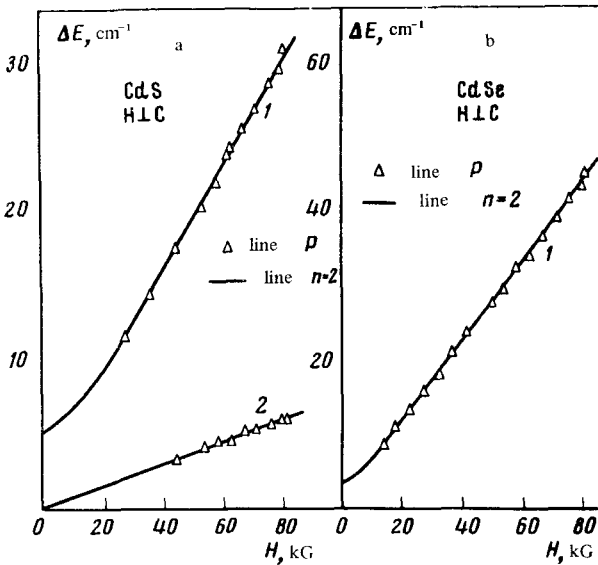


FIG. 3. Comparison of the orbital (1) and spin (2) splittings of the Zeeman components of the  $P$  lines (triangles) and  $n=2$  lines (solid): a—CdS, b—CdSe.

diamagnetic shift has been established, which was determined by subtracting the quadratic shift of the corresponding components of the state  $n=2$  from the experimentally established shift of the Zeeman components of the  $P$  line. The diamagnetic shift turns out to be substantially anisotropic (for CdS:  $d_1 = 6 \times 10^{-10}$  and  $d_{11} = 9.4 \times 10^{-10} \text{ cm}^{-1} \text{ G}^{-2}$ ), as expected of hexagonal crystals in which the wave function of the biexcitons should be flattened in the direction of the  $c$  axis. The diamagnetic shift itself is much larger than double the diamagnetic shift of the exciton level  $n=1$ , and consequently the  $P$  line cannot be attributed to collision of two free excitons. Thus, the magneto-optical experiments enable us to establish that the  $P$  line is indeed due to radiative decay of a biexciton with a transfer of the remaining exciton into the excited state  $n=2$ .

4. In principle, the radiative decay of a biexciton with formation of an exciton in various quantum states could lead to observation of an inverted series of emission lines ( $M \rightarrow n=1, 2, 3, \dots \infty$ ), shifted to the low-energy side of the exciton level  $n=1$  by an amount equal to the binding energy of the molecule. However, as follows from Buttner's work<sup>[9]</sup> the intensity of the transitions to excited states ( $n > 1$ ) decreases rapidly with increasing quantum number. Indeed, in our experiments one observes distinctly the transition  $M \rightarrow n=2$ , while the transition  $M \rightarrow n=3$  is hardly noticeable. An important experimental fact is the absence, at high excitation intensities, of noticeable emission lines, which might be interpreted as  $M \rightarrow n=1$  transitions. This may be caused by two effects. The probability of the process  $M \rightarrow n=1$  is proportional to the square of the modulus of the Fourier component of the wave function of the relative motion of the excitons in the biexciton<sup>[10]</sup>

$$W(Q) \sim \left| \psi_m \left( \frac{Q}{2} \right) \right|^2,$$

where  $Q$  is the wave vector of the biexciton. The calculation of  $W(Q)$  using the wave function of the biexciton from<sup>15</sup> reveals a sharp decrease of  $W(Q)$  with increasing  $Q$ , and this leads to a decrease of the probability of the  $M \rightarrow n=1$  transitions. On the other hand, in the region of low values of  $Q$  one should expect a decrease of the probability of the  $M \rightarrow n=1$  transition, owing to the optical-exciton interaction in the states  $n=1$ .<sup>11,12</sup>

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<sup>1</sup>An analysis for magnetic fields up to 35 kG was also carried out on the basis of perturbation theory in<sup>6,7</sup>.

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